

MOSFETs Silicon N-Channel MOS ( $\pi$ -MOSVII)

# TK5P53D

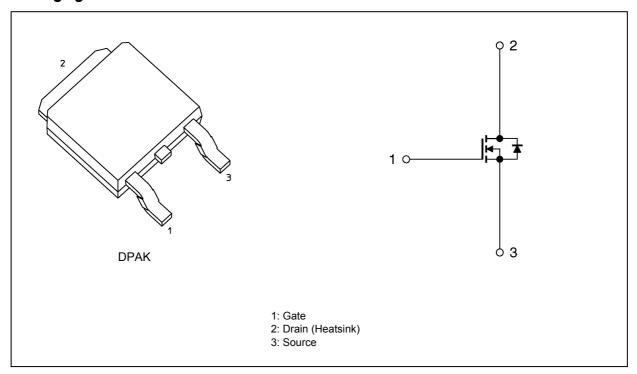
#### 1. Applications

• Switching Voltage Regulators

#### 2. Features

- (1) Low drain-source on-resistance :  $R_{DS(ON)} = 1.2 \Omega$  (typ.)
- (2) High forward transfer admittance :  $|Y_{fs}| = 2.8 \text{ S (typ.)}$
- (3) Low leakage current :  $I_{DSS}$  = 10  $\mu A$  (max) ( $V_{DS}$  = 525 V)
- (4) Enhancement mode :  $V_{th}$  = 2.4 to 4.4 V ( $V_{DS}$  = 10 V,  $I_{D}$  = 1 mA)

### 3. Packaging and Internal Circuit





### 4. Absolute Maximum Ratings (Note) (Ta = 25 °C unless otherwise specified)

Characteristics			Symbol	Rating	Unit
Drain-source voltage			$V_{DSS}$	525	V
Gate-source voltage			$V_{GSS}$	±30	
Drain current (DC)	(N	lote 1)	I <sub>D</sub>	5	Α
Drain current (pulsed)	(N	lote 1)	I <sub>DP</sub>	20	
Power dissipation	(T <sub>c</sub> = 25 °C)		$P_{D}$	80	W
Single-pulse avalanche energy	(N	lote 2)	E <sub>AS</sub>	142	mJ
Avalanche current	(N	lote 3)	I <sub>AR</sub>	5	Α
Repetitive avalanche energy	(N	lote 3)	E <sub>AR</sub>	8	mJ
Reverse drain current (DC)	(N	lote 1)	I <sub>DR</sub>	5	Α
Reverse drain current (pulsed)	(N	lote 1)	I <sub>DRP</sub>	20	
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R <sub>th(ch-c)</sub>	1.56	°C/W
Channel-to-ambient thermal resistance	R <sub>th(ch-a)</sub>	125	

Note 1: Ensure that the channel temperature does not exceed 150 °C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25 °C (initial), L = 9.72 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 5 A

Note 3: Repetitive rating; pulse width limited by maximum channel temperature.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



#### 6. Electrical Characteristics

### 6.1. Static Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±1	μΑ
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 525 V, V <sub>GS</sub> = 0 V	_	_	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	525	_	_	V
Gate threshold voltage	$V_{th}$	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	2.4	_	4.4	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 2.5 A	_	1.2	1.5	Ω
Forward transfer admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 2.5 A	0.7	2.8	_	S

### 6.2. Dynamic Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V,	_	540	_	pF
Reverse transfer capacitance	C <sub>rss</sub>	f = 1 MHz	_	3	_	
Output capacitance	C <sub>oss</sub>		_	60	_	
Switching time (rise time)	t <sub>r</sub>	See Fig.6.2.1	_	18	_	ns
Switching time (turn-on time)	t <sub>on</sub>		_	40	_	
Switching time (fall time)	t <sub>f</sub>		_	8	_	
Switching time (turn-off time)	t <sub>off</sub>		_	55	_	

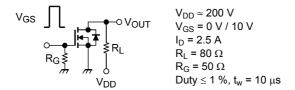


Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	$Q_g$	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V},$	_	11	_	nC
Gate-source charge	$Q_{gs}$	I <sub>D</sub> = 5 A	_	6	_	
Gate-drain charge	$Q_{gd}$		_	5	_	

### 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25 °C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Diode forward voltage	$V_{DSF}$	I <sub>DR</sub> = 5 A, V <sub>GS</sub> = 0 V	_	_	-1.7	V
Reverse recovery time	• • • • • • • • • • • • • • • • • • • •	I <sub>DR</sub> = 5 A, V <sub>GS</sub> = 0 V,	_	1000	_	ns
Reverse recovery charge	Q <sub>rr</sub>	-di/dt = 100 A/μs	_	6	_	μС



### 7. Marking

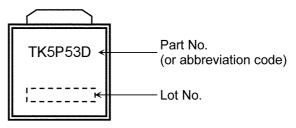


Fig. 7.1 Marking

#### 8. Characteristics Curves (Note)

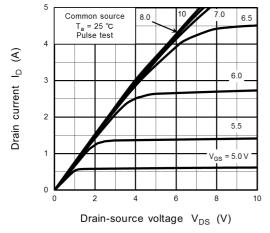


Fig. 8.1 I<sub>D</sub> - V<sub>DS</sub>

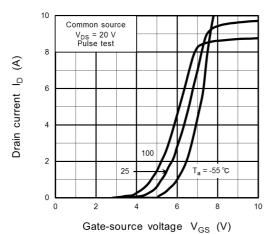


Fig. 8.3 I<sub>D</sub> - V<sub>GS</sub>

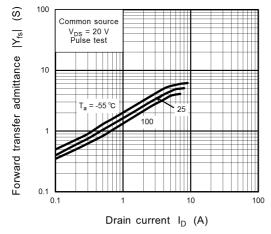


Fig. 8.5 |Y<sub>fs</sub>| - I<sub>D</sub>

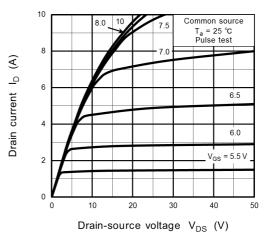


Fig. 8.2 I<sub>D</sub> - V<sub>DS</sub>

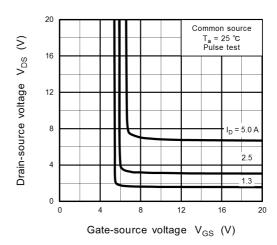


Fig. 8.4 V<sub>DS</sub> - V<sub>GS</sub>

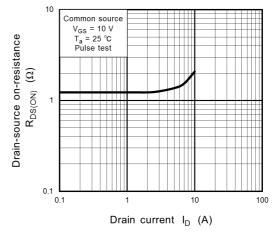


Fig. 8.6 R<sub>DS(ON)</sub> - I<sub>D</sub>

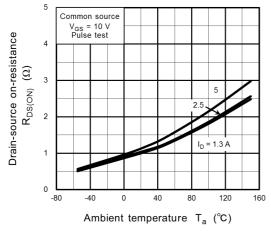


Fig. 8.7 R<sub>DS(ON)</sub> - T<sub>a</sub>

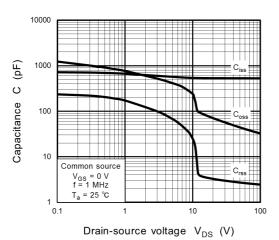


Fig. 8.9 C - V<sub>DS</sub>

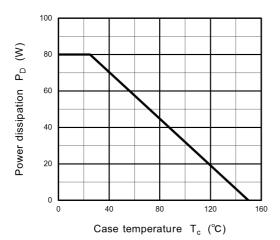


Fig. 8.11 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

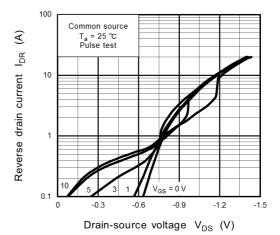


Fig. 8.8 I<sub>DR</sub> - V<sub>DS</sub>

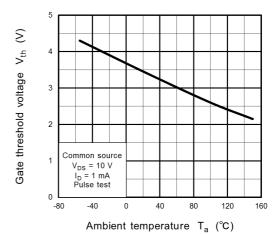


Fig. 8.10 V<sub>th</sub> - T<sub>a</sub>

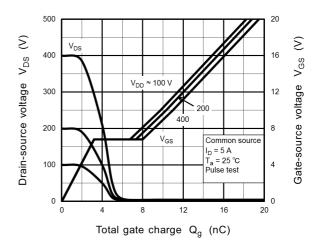


Fig. 8.12 Dynamic Input/Output Characteristics

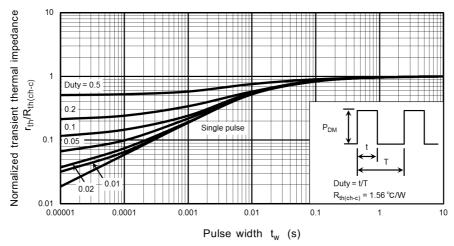


Fig. 8.13  $r_{th}/R_{th(ch-c)} - t_w$  (Guaranteed Maximum)

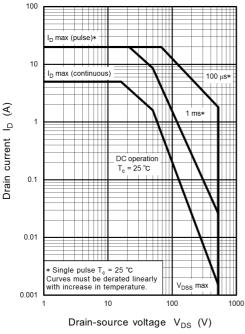


Fig. 8.14 Safe Operating Area (Guaranteed Maximum)

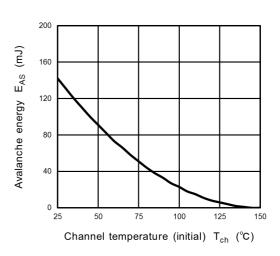


Fig. 8.15 E<sub>AS</sub> - T<sub>ch</sub> (Guaranteed Maximum)

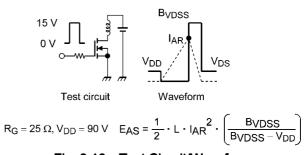


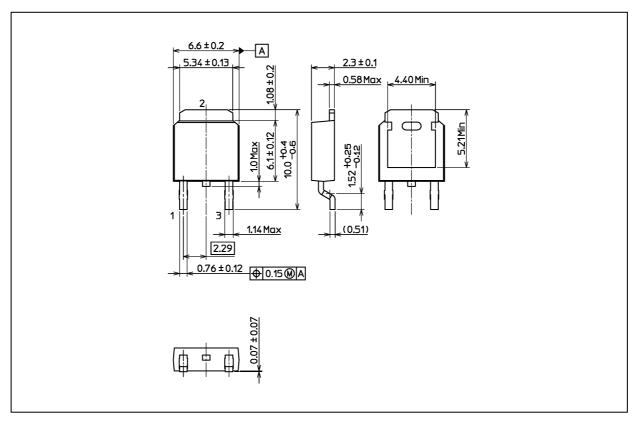
Fig. 8.16 Test Circuit/Waveform

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### **Package Dimensions**

Unit: mm



Both products are compliant with the JEDEC: TO-252 Package specification. Please contact the Toshiba sales representative for further details.

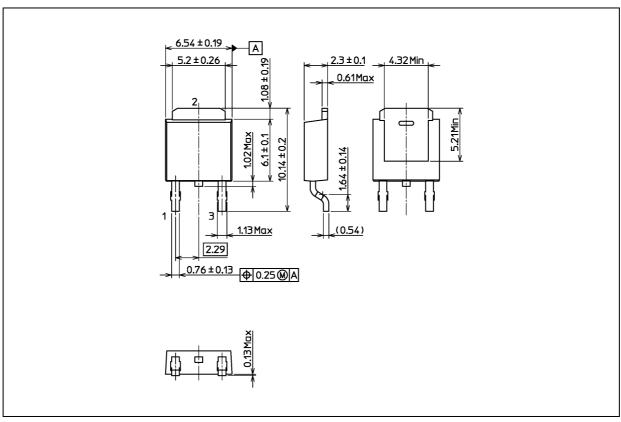
Weight: 0.36 g (typ.)

	Package Name(s)
JEDEC: TO-252	
TOSHIBA: 2-7K1S	
Nickname: DPAK	



### **Package Dimensions**

Unit: mm



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Weight: 0.389 g (typ.)

Package Name(s)
JEDEC: TO-252
TOSHIBA: 2-7N1S
Nickname: DPAK



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